



Description

The IRF7420TRPBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -20V$ $I_D = -20A$

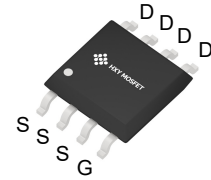
$R_{DS(ON)} < 19m\Omega @ V_{GS}=10V$

Application

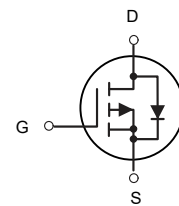
Battery protection

Load switch

Uninterruptible power supply



SOP-8
(SOIC-8)



P-Channel MOSFET

Ordering Information

Product ID	Pack	Brand	Qty(PCS)
IRF7420TRPBF	SOP-8(SOIC-8)	HXY MOSFET	3000

Absolute Maximum Ratings($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_A=25^\circ C$	Drain Current ³ , $V_{GS} @ 10V$	-20	A
$I_D @ T_A=70^\circ C$	Drain Current ³ , $V_{GS} @ 10V$	-16	A
I_{DM}	Pulsed Drain Current ¹	-68	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation	18	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient ³	75	$^\circ C/W$



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.012	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-10A	---	15	19	mΩ
		V _{GS} =-2.5V, I _D =-8A	---	19	23	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.4	-0.7	-1.0	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	2.94	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-15V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-10A	---	43	---	S
Q _g	Total Gate Charge (-4.5V)		---	35	---	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-10A	---	5.0	---	
Q _{gd}	Gate-Drain Charge		---	10	---	
T _{d(on)}	Turn-On Delay Time		---	12.0	---	ns
T _r	Rise Time	V _{DD} =-10V, V _{GS} =-4.5V,	---	40.0	---	
T _{d(off)}	Turn-Off Delay Time	R _G =3.3Ω, I _D =-10A	---	30	---	
T _f	Fall Time		---	10	---	
C _{iss}	Input Capacitance		---	2800	---	pF
C _{oss}	Output Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	690	---	
C _{rss}	Reverse Transfer Capacitance		---	590	---	
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-20.0	A
I _{SM}	Pulsed Source Current ^{2,4}		---	---	---	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-10A, dI/dt=100A/μs,	---	27	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25°C	---	17.8	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

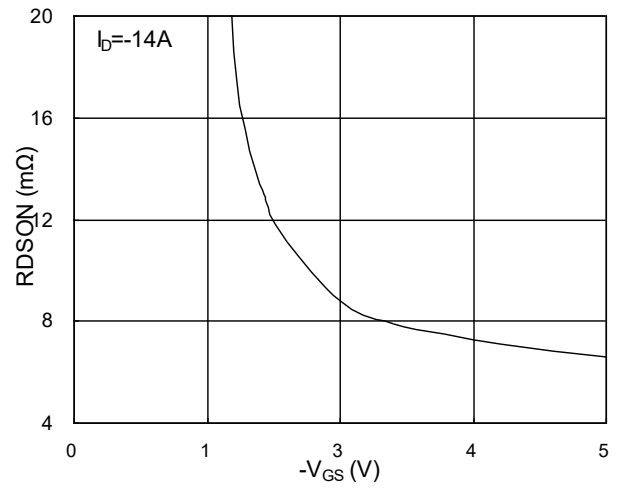
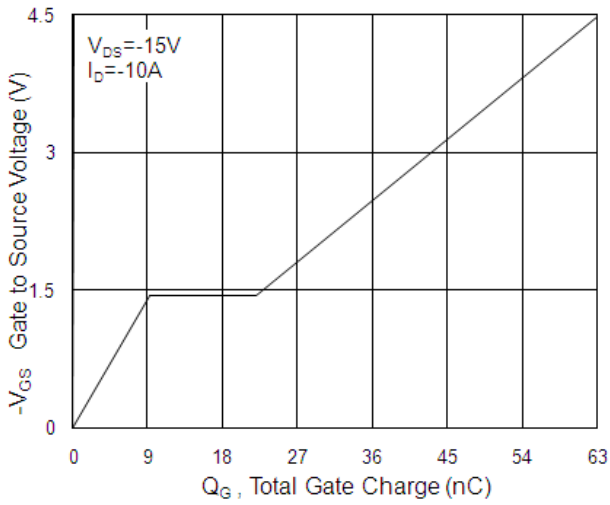


Fig.1 Typical Output Characteristics

Fig.2 On-Resistance vs. G-S Voltage

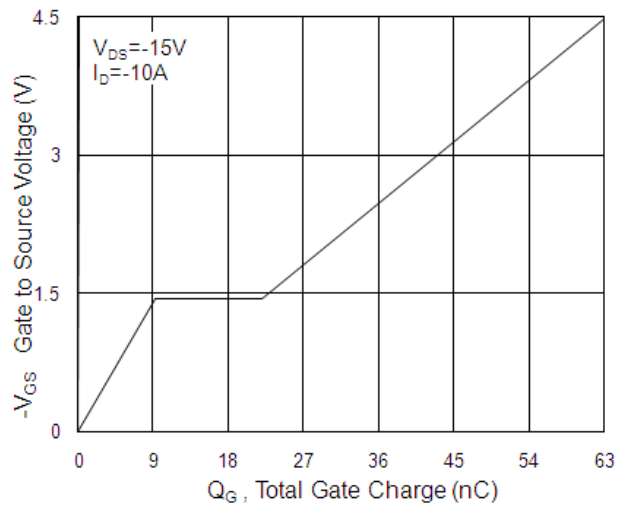
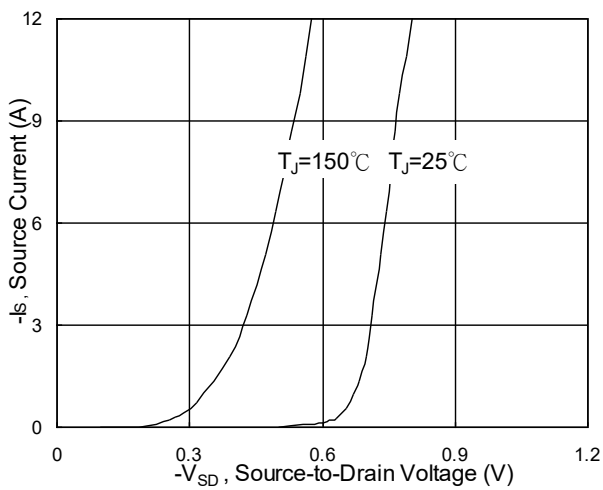


Fig.3 Forward Characteristics of Reverse

Fig.4 Gate-charge Characteristics

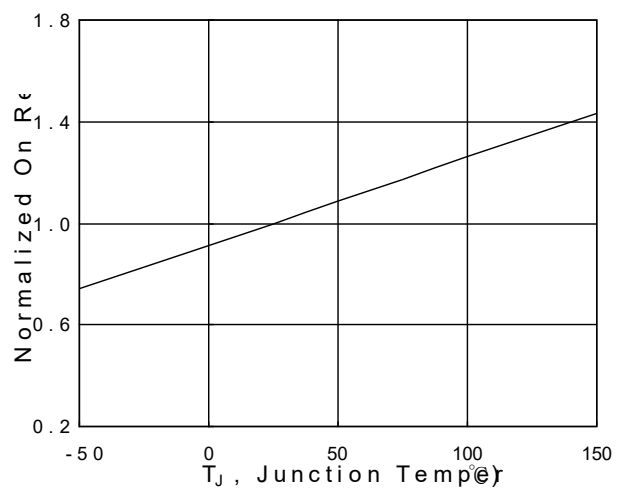
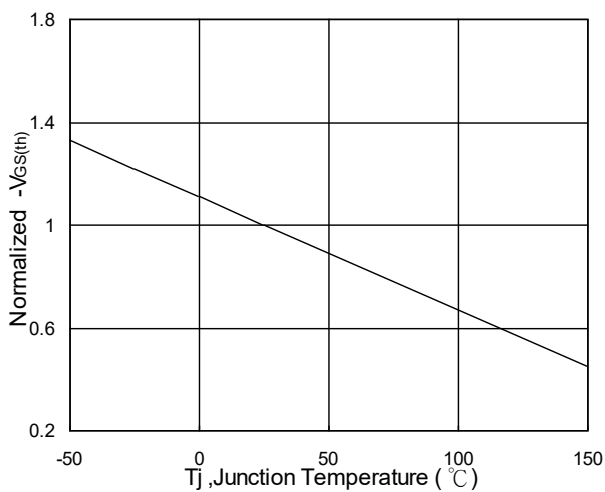


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

Fig.6 Normalized $R_{DS(on)}$ vs. T_J

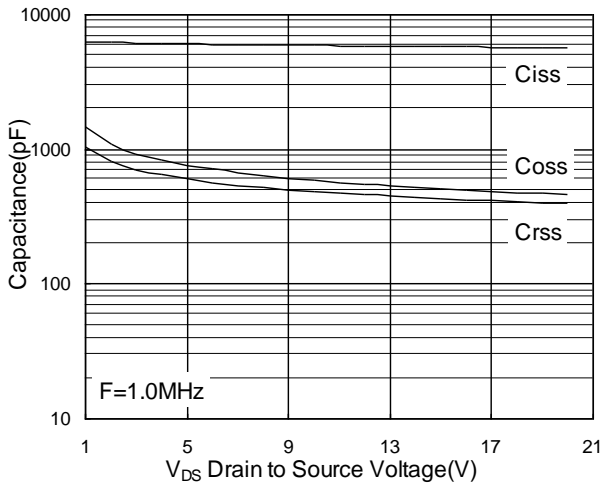


Fig.7 Capacitance

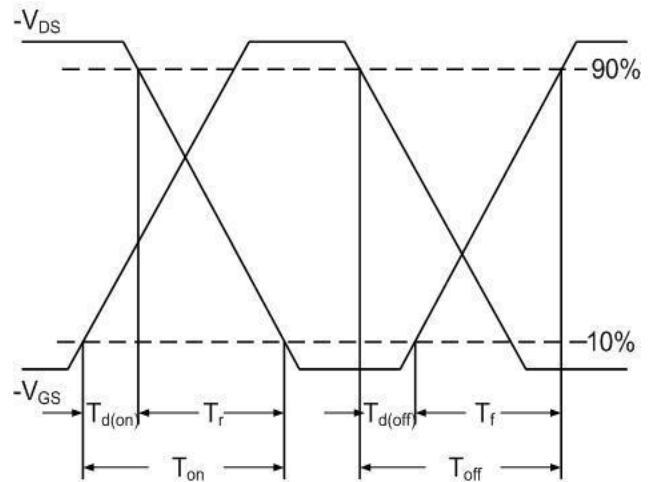


Fig.8 Safe Operating Area

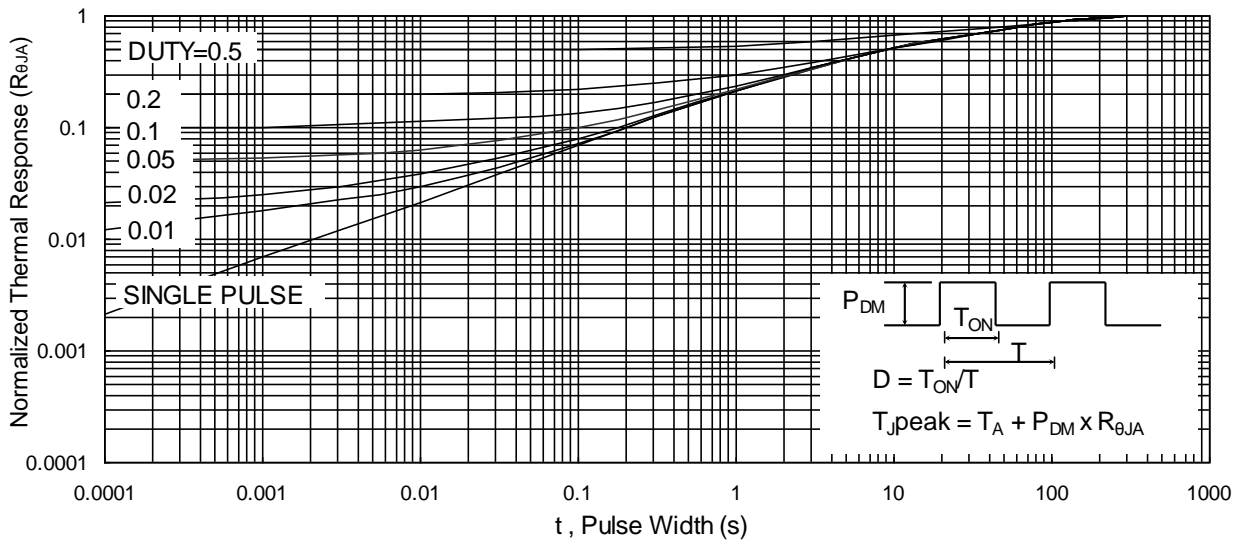


Fig.9 Normalized Maximum Transient Thermal Impedance

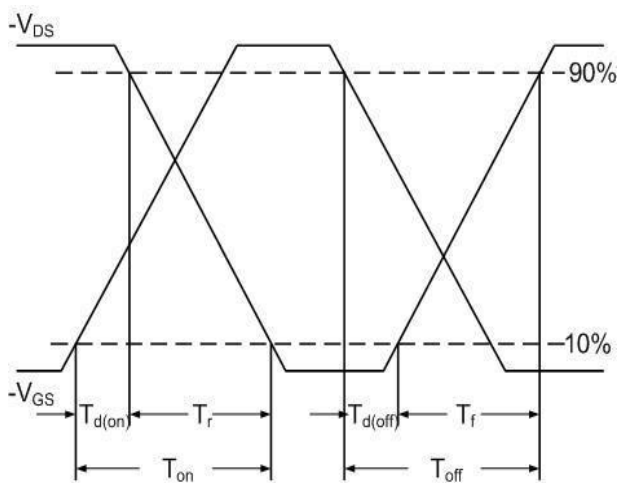


Fig.10 Switching Time Waveform

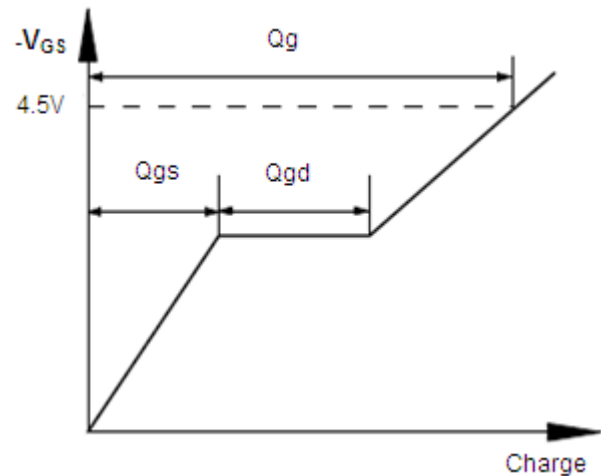


Fig.11 Gate Charge Waveform



SOP-8(SOIC-8) Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
 1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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